MC100LVEL51

3.3 V ECL Differential Clock D Flip-Flop

Description

The MC100LVEL51 is a differential clock D flip-flop with reset. The device is functionally equivalent to the EL51 device, but operates from a 3.3 V supply. With propagation delays and output transition times essentially equal to the EL51, the LVEL51 is ideally suited for those applications which require the ultimate in AC performance at 3.3 V V_{CC}.

The reset input is an asynchronous, level triggered signal. Data enters the master portion of the flip-flop when the clock is LOW and is transferred to the slave, and thus the outputs, upon a positive transition of the clock. The differential clock inputs of the LVEL51 allow the device to be used as a negative edge triggered flip-flop.

The differential input employs clamp circuitry to maintain stability under open input conditions. When left open, the CLK input will be pulled down to V_{EE} and the $\overline{CLK}$ input will be biased at $V_{CC}/2$.

Features

- 475 ps Propagation Delay
- 2.8 GHz Toggle Frequency
- ESD Protection: > 4 kV Human Body Model,
  > 200 V Machine Model
- The 100 Series Contains Temperature Compensation
- PECL Mode Operating Range: V_{CC} = 3.0 V to 3.8 V
  with V_{EE} = 0 V
- NECL Mode Operating Range: V_{CC} = 0 V
  with V_{EE} = −3.0 V to −3.8 V
- Internal Input Pulldown Resistors
- Meets or Exceeds JEDEC Spec EIA/JESD78 IC Latchup Test
- Moisture Sensitivity Level
  - ♦ Level 1 for SOIC−8 NB
  - ♦ Level 3 for TSSOP−8
  - ♦ Level 1 for DFN−8
  - ♦ For Additional Information, see Application Note AND8003/D
- Flammability Rating: UL 94 V−0 @ 0.125 in,
  Oxygen Index: 28 to 34
- Transistor Count = 114 devices
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant
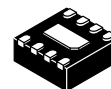
ON Semiconductor®

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8 ▬ 1	8 ▬ 1	▬
SOIC−8 NB D SUFFIX CASE 751	**TSSOP−8 DT SUFFIX CASE 948R**	**DFN−8 MN SUFFIX CASE 506AA**

MARKING DIAGRAMS*

SOIC−8	TSSOP−8	DFN−8
KVL51 ALYW	KV51 ALYW	4G $\overline{M}$
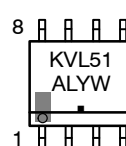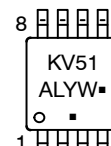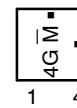
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
$\overline{M}$ = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

Device	Package	Shipping†
MC100LVEL51DG	SOIC−8 NB (Pb-Free)	98 Units/Tube
MC100LVEL51DR2G	SOIC−8 NB (Pb-Free)	2500/Tape & Reel
MC100LVEL51DTG	TSSOP−8 (Pb-Free)	100 Units/Tube
MC100LVEL51DTR2G	TSSOP−8 (Pb-Free)	2500/Tape & Reel
MC100LVEL51MNR4G	DFN−8 (Pb-Free)	1000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
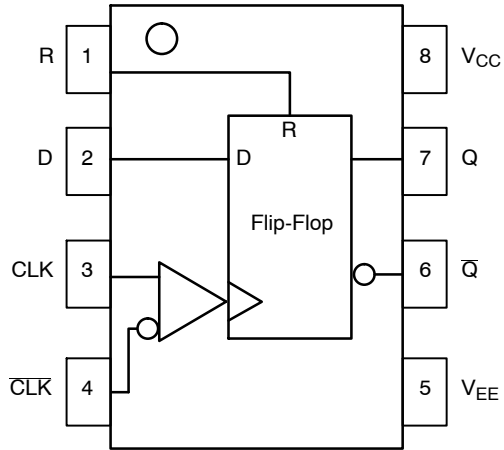
MC100LVEL51

Figure 1. Logic Diagram and Pinout Assignment

Table 1. PIN DESCRIPTION

PIN	FUNCTION
CLK, $\overline{\text{CLK}}$	ECL Differential Clock Input
Q, $\overline{\text{Q}}$	ECL Differential Output
D	ECL D Input
R	ECL Reset Input
V_{CC}	Positive Supp;y
V_{EE}	Negative Supply
EP	(DFN8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

Table 2. TRUTH TABLE

D	R	CLK	Q
L	L	Z	L
H	L	Z	H
X	H	X	L

Z = LOW to HIGH Transition
X = Don't Care

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	PECL Mode Power Supply	V_{EE} = 0 V		8 to 0	V
V_{EE}	NECL Mode Power Supply	V_{CC} = 0 V		−8 to 0	V
V_I	PECL Mode Input Voltage NECL Mode Input Voltage	V_{EE} = 0 V V_{CC} = 0 V	$V_I \leq V_{CC}$ $V_I \geq V_{EE}$	6 to 0 −6 to 0	V
I_{out}	Output Current	Continuous Surge		50 100	mA
T_A	Operating Temperature Range			−40 to +85	°C
T_{stg}	Storage Temperature Range			−65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC−8 NB	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC−8 NB	41 to 44 ± 5%	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP−8	185 140	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP−8	41 to 44 ± 5%	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN−8	129 84	°C/W
T_{sol}	Wave Solder (Pb-Free)	< 2 to 3 sec @ 260°C		265	°C
θ_{JC}	Thermal Resistance (Junction-to-Case)	(Note 1)	DFN−8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. JEDEC standard multilayer board − 2S2P (2 signal, 2 power)

Table 4. LVPECL DC CHARACTERISTICS (V_{CC} = 3.3 V; V_{EE} = 0.0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current		30	35		30	35		32	37	mA
V_{OH}	Output HIGH Voltage (Note 2)	2215	2295	2420	2275	2345	2420	2275	2345	2420	mV
V_{OL}	Output LOW Voltage (Note 2)	1470	1605	1745	1490	1595	1680	1490	1595	1680	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	2135		2420	2135		2420	2135		2420	mV
V_{IL}	Input LOW Voltage (Single-Ended)	1490		1825	1490		1825	1490		1825	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential) (Note 3) V_{PP} < 500 mV V_{PP} ≥ 500 mV	1.2 1.4		3.0 3.0	1.1 1.3		3.0 3.0	1.1 1.3		3.0 3.0	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current Others $\overline{CLK}$	0.5 −600			0.5 −600			0.5 −600			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary ±0.3 V.
2. Outputs are terminated through a 50 Ω resistor to V_{CC} − 2.0 V.
3. V_{IHCMR} min varies 1:1 with V_{EE}, max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP}min and 1 V.

Table 5. LVNECL DC CHARACTERISTICS (V_{CC} = 0.0 V; V_{EE} = −3.3 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current		30	35		30	35		32	37	mA
V_{OH}	Output HIGH Voltage (Note 2)	−1085	−1005	−880	−1025	−955	−880	−1025	−955	−880	mV
V_{OL}	Output LOW Voltage (Note 2)	−1830	−1695	−1555	−1810	−1705	−1620	−1810	−1705	−1620	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	−1165		−880	−1165		−880	−1165		−880	mV
V_{IL}	Input LOW Voltage (Single-Ended)	−1810		−1475	−1810		−1475	−1810		−1475	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential) (Note 3) V_{PP} < 500 mV V_{PP} ≥ 500 mV	−2.1 −1.9		−0.3 −0.3	−2.2 −2.0		−0.3 −0.3	−2.2 −2.0		−0.3 −0.3	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current Others $\overline{CLK}$	0.5 −600			0.5 −600			0.5 −600			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary ±0.3 V.
2. Outputs are terminated through a 50 Ω resistor to V_{CC} − 2.0 V.
3. V_{IHCMR} min varies 1:1 with V_{EE}, max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP}min and 1 V.

MC100LVEL51

Table 6. AC CHARACTERISTICS (V_{CC} = 3.3 V; V_{EE} = 0.0 V or V_{CC} = 0.0 V; V_{EE} = −3.3 V (Note 1))

Symbol	Characteristic	−40°C Min	Typ	Max	25°C Min	Typ	Max	85°C Min	Typ	Max	Unit
f_{max}	Maximum Toggle Frequency	2.7			2.8			2.9			GHz
t_{PLH} t_{PHL}	Propagation Delay to Output CLK R	330 340	465 455	510 540	340 350	475 465	520 550	370 390	530 510	550 590	ps
t_S	Setup Time	150	0		150	0		150	0		ps
t_H	Hold Time	200	100		200	100		200	100		ps
t_{RR}	Reset Recovery	350	200		350	200		350	200		ps
t_{PW}	Minimum Pulse CLK Width Reset	400 500			400 500			400 500			ps
t_{JITTER}	Cycle-to-Cycle Jitter		TBD			TBD			TBD		ps
V_{PP}	Input Swing (Note 2)	150		1000	150		1000	150		1000	mV
t_r t_f	Output Rise/Fall Times Q (20% – 80%)	120		320	120		320	120		320	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.
1. V_{EE} can vary ±0.3 V.
2. V_{PP} (min) is minimum input swing for which AC parameters are guaranteed.
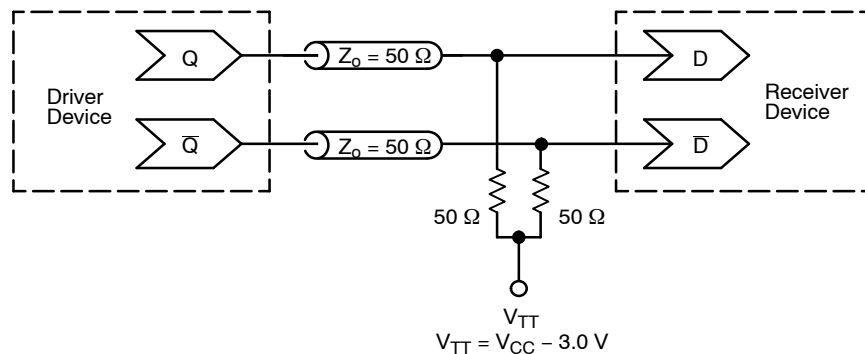
Figure 2. Typical Termination for Output Driver and Device Evaluation
(See Application Note AND8020/D – Termination of ECL Logic Devices.)

Resource Reference of Application Notes

AN1405/D – ECL Clock Distribution Techniques

AN1406/D – Designing with PECL (ECL at +5.0 V)

AN1503/D – ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D – Metastability and the ECLinPS Family

AN1568/D – Interfacing Between LVDS and ECL

AN1672/D – The ECL Translator Guide

AND8001/D – Odd Number Counters Design

AND8002/D – Marking and Date Codes

AND8020/D – Termination of ECL Logic Devices

AND8066/D – Interfacing with ECLinPS

AND8090/D – AC Characteristics of ECL Devices

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MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS
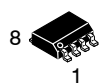
SOIC−8 NB
CASE 751−07
ISSUE AK

DATE 16 FEB 2011
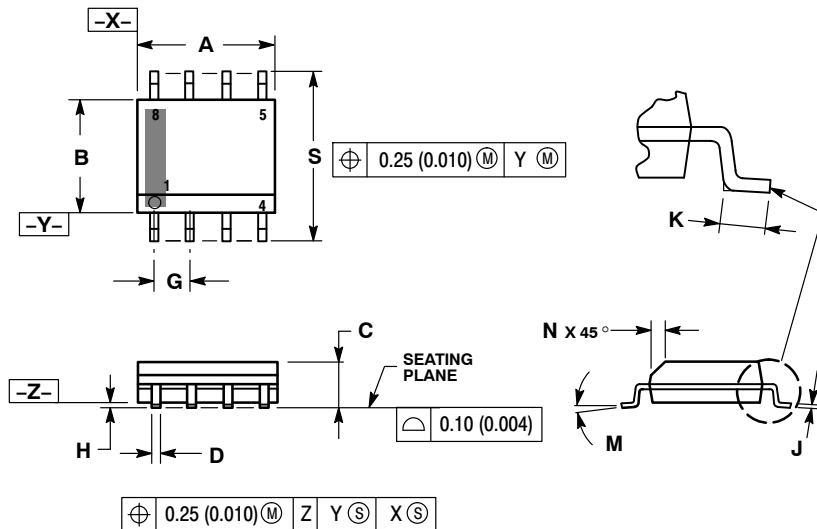
8
1
SCALE 1:1

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

$\boxed{\bigoplus\ 0.25\ (0.010)\ \text{\small M}\quad Y\ \text{\small M}}$

$\boxed{\bigoplus\ 0.25\ (0.010)\text{\small M}\quad Z\quad Y\ \text{\small S}\quad X\ \text{\small S}}$

SEATING PLANE

$\boxed{\triangle\ 0.10\ (0.004)}$

DIM	MILLIMETERS		INCHES	
	MIN	**MAX**	**MIN**	**MAX**
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*

1.52 / 0.060

7.0 / 0.275

4.0 / 0.155

0.6 / 0.024

1.270 / 0.050

SCALE 6:1 $\left(\dfrac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

IC

IC (Pb−Free)

Discrete

Discrete (Pb−Free)
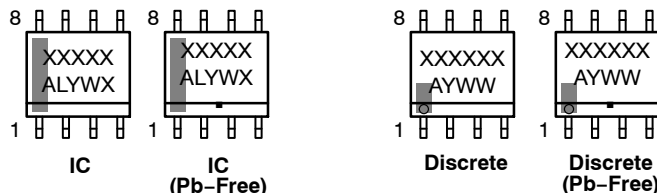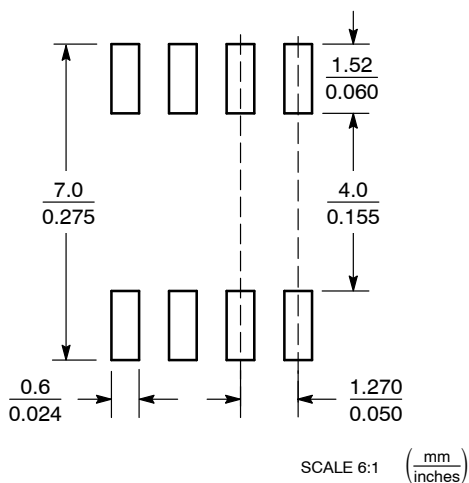
XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

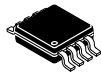| DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC−8 NB		PAGE 1 OF 2

STYLE 1:
PIN 1. EMITTER
 2. COLLECTOR
 3. COLLECTOR
 4. EMITTER
 5. EMITTER
 6. BASE
 7. BASE
 8. EMITTER

STYLE 2:
PIN 1. COLLECTOR, DIE, #1
 2. COLLECTOR, #1
 3. COLLECTOR, #2
 4. COLLECTOR, #2
 5. BASE, #2
 6. EMITTER, #2
 7. BASE, #1
 8. EMITTER, #1

STYLE 3:
PIN 1. DRAIN, DIE #1
 2. DRAIN, #1
 3. DRAIN, #2
 4. DRAIN, #2
 5. GATE, #2
 6. SOURCE, #2
 7. GATE, #1
 8. SOURCE, #1

STYLE 4:
PIN 1. ANODE
 2. ANODE
 3. ANODE
 4. ANODE
 5. ANODE
 6. ANODE
 7. ANODE
 8. COMMON CATHODE

STYLE 5:
PIN 1. DRAIN
 2. DRAIN
 3. DRAIN
 4. DRAIN
 5. GATE
 6. GATE
 7. SOURCE
 8. SOURCE

STYLE 6:
PIN 1. SOURCE
 2. DRAIN
 3. DRAIN
 4. SOURCE
 5. SOURCE
 6. GATE
 7. GATE
 8. SOURCE

STYLE 7:
PIN 1. INPUT
 2. EXTERNAL BYPASS
 3. THIRD STAGE SOURCE
 4. GROUND
 5. DRAIN
 6. GATE 3
 7. SECOND STAGE Vd
 8. FIRST STAGE Vd

STYLE 8:
PIN 1. COLLECTOR, DIE #1
 2. BASE, #1
 3. BASE, #2
 4. COLLECTOR, #2
 5. COLLECTOR, #2
 6. EMITTER, #2
 7. EMITTER, #1
 8. COLLECTOR, #1

STYLE 9:
PIN 1. EMITTER, COMMON
 2. COLLECTOR, DIE #1
 3. COLLECTOR, DIE #2
 4. EMITTER, COMMON
 5. EMITTER, COMMON
 6. BASE, DIE #2
 7. BASE, DIE #1
 8. EMITTER, COMMON

STYLE 10:
PIN 1. GROUND
 2. BIAS 1
 3. OUTPUT
 4. GROUND
 5. GROUND
 6. BIAS 2
 7. INPUT
 8. GROUND

STYLE 11:
PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. DRAIN 2
 7. DRAIN 1
 8. DRAIN 1

STYLE 12:
PIN 1. SOURCE
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN

STYLE 13:
PIN 1. N.C.
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN

STYLE 14:
PIN 1. N−SOURCE
 2. N−GATE
 3. P−SOURCE
 4. P−GATE
 5. P−DRAIN
 6. P−DRAIN
 7. N−DRAIN
 8. N−DRAIN

STYLE 15:
PIN 1. ANODE 1
 2. ANODE 1
 3. ANODE 1
 4. ANODE 1
 5. CATHODE, COMMON
 6. CATHODE, COMMON
 7. CATHODE, COMMON
 8. CATHODE, COMMON

STYLE 16:
PIN 1. EMITTER, DIE #1
 2. BASE, DIE #1
 3. EMITTER, DIE #2
 4. BASE, DIE #2
 5. COLLECTOR, DIE #2
 6. COLLECTOR, DIE #2
 7. COLLECTOR, DIE #1
 8. COLLECTOR, DIE #1

STYLE 17:
PIN 1. VCC
 2. V2OUT
 3. V1OUT
 4. TXE
 5. RXE
 6. VEE
 7. GND
 8. ACC

STYLE 18:
PIN 1. ANODE
 2. ANODE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. CATHODE
 8. CATHODE

STYLE 19:
PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. MIRROR 2
 7. DRAIN 1
 8. MIRROR 1

STYLE 20:
PIN 1. SOURCE (N)
 2. GATE (N)
 3. SOURCE (P)
 4. GATE (P)
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN

STYLE 21:
PIN 1. CATHODE 1
 2. CATHODE 2
 3. CATHODE 3
 4. CATHODE 4
 5. CATHODE 5
 6. COMMON ANODE
 7. COMMON ANODE
 8. CATHODE 6

STYLE 22:
PIN 1. I/O LINE 1
 2. COMMON CATHODE/VCC
 3. COMMON CATHODE/VCC
 4. I/O LINE 3
 5. COMMON ANODE/GND
 6. I/O LINE 4
 7. I/O LINE 5
 8. COMMON ANODE/GND

STYLE 23:
PIN 1. LINE 1 IN
 2. COMMON ANODE/GND
 3. COMMON ANODE/GND
 4. LINE 2 IN
 5. LINE 2 OUT
 6. COMMON ANODE/GND
 7. COMMON ANODE/GND
 8. LINE 1 OUT

STYLE 24:
PIN 1. BASE
 2. EMITTER
 3. COLLECTOR/ANODE
 4. COLLECTOR/ANODE
 5. CATHODE
 6. CATHODE
 7. COLLECTOR/ANODE
 8. COLLECTOR/ANODE

STYLE 25:
PIN 1. VIN
 2. N/C
 3. REXT
 4. GND
 5. IOUT
 6. IOUT
 7. IOUT
 8. IOUT

STYLE 26:
PIN 1. GND
 2. dv/dt
 3. ENABLE
 4. ILIMIT
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. VCC

STYLE 27:
PIN 1. ILIMIT
 2. OVLO
 3. UVLO
 4. INPUT+
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. DRAIN

STYLE 28:
PIN 1. SW_TO_GND
 2. DASIC_OFF
 3. DASIC_SW_DET
 4. GND
 5. V_MON
 6. VBULK
 7. VBULK
 8. VIN

STYLE 29:
PIN 1. BASE, DIE #1
 2. EMITTER, #1
 3. BASE, #2
 4. EMITTER, #2
 5. COLLECTOR, #2
 6. COLLECTOR, #2
 7. COLLECTOR, #1
 8. COLLECTOR, #1

STYLE 30:
PIN 1. DRAIN 1
 2. DRAIN 1
 3. GATE 2
 4. SOURCE 2
 5. SOURCE 1/DRAIN 2
 6. SOURCE 1/DRAIN 2
 7. SOURCE 1/DRAIN 2
 8. GATE 1

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DESCRIPTION:	SOIC−8 NB		PAGE 2 OF 2

TSSOP 8
CASE 948R−02
ISSUE A

DATE 04/07/2000

SCALE 2:1

8x **K** REF

⊕ | 0.10 (0.004) Ⓜ | T | U Ⓢ | V Ⓢ

0.15 (0.006) | T | U Ⓢ

2X **L/2**

L

8   5

B
−U−

PIN 1
IDENT

1   4

0.15 (0.006) | T | U Ⓢ

A
−V−

0.25 (0.010)

M

F

DETAIL E

C

0.10 (0.004)

−T− SEATING
PLANE

D   **G**

−W−

DETAIL E

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
M	0°	6°	0°	6°

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